

N Channel Power MOSFET FOR LOGIC DRIVER

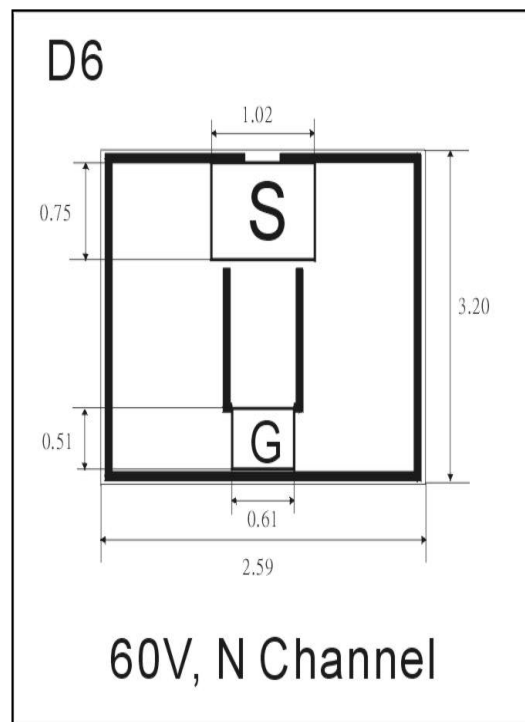
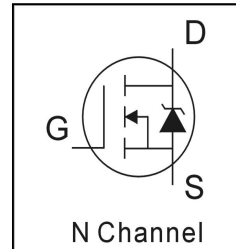
Chip Specification

General Description:

- * Advanced Process Technology
- * Dynamic dv/dt Rating
- * **175°C Operating Temperature**
- * **Fast Switching**
- * **Fully Avalanche Rated**
- * **RDS(ON) rated at VGS = 5V**
- * **Ease of parallel**

Mechanical Data:

D6	
Dimension	2.59mm x3.20mm
Thickness:	400 μm
Metallization:	
Top :	Al
Backside :	CrNiAg / Au
Suggested Bonding Conditions:	
Die Mounting:	Solder Perform
	95/5 PbSn or 92.5/2.5/5 PbAgIn
Source Bonding Wire:	10 mil Al



Absolute Maximum Rating

@Ta=25°C

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	60	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	0.1	Ω	VGS=5V, ID=10A
Continuous Drain current (in target package)	ID@25°C	17	A	VGS= 5V
Continuous Drain current (in target package)	ID@100°C	12	A	VGS= 5V
Operation Junction Temperature	Tj	-55~175	°C	
Storage Temperature	TSTR	-55~175	°C	

Target Device: IRLZ24

TO-220AB

Pd

60

W

@Tc=25°C

